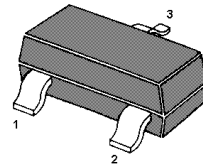


MMBTSA1037

PNP Silicon Epitaxial Planar Transistor

The transistor is subdivided into three groups Q, R and S according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1.BASE 2.EMITTER 3.COLLECTOR
SOT-23 Plastic Package

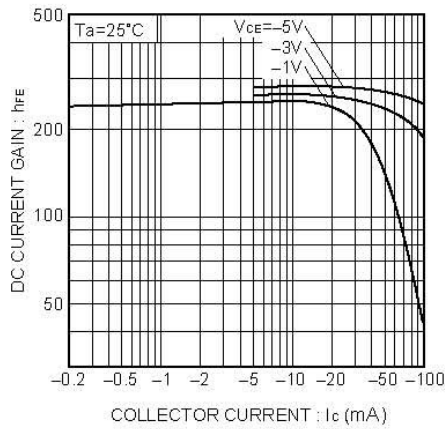
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	60	V
Collector Emitter Voltage	$-V_{CEO}$	50	V
Emitter Base Voltage	$-V_{EBO}$	6	V
Collector Current	$-I_C$	150	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

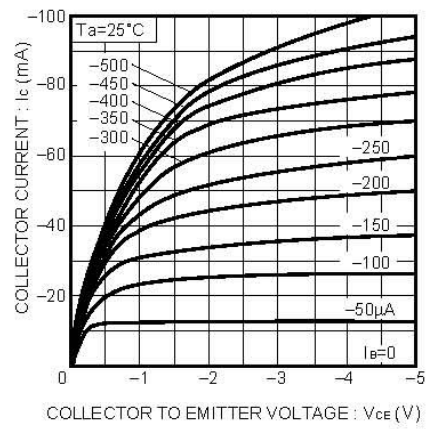
Characteristics at $T_{amb}=25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $-V_{CE} = 6\text{ V}$, $-I_C = 1\text{ mA}$ Current Gain Group	Q	h_{FE}	120	-	270	-
	R	h_{FE}	180	-	390	-
	S	h_{FE}	270	-	560	-
Collector Base Cutoff Current at $-V_{CB} = 60\text{ V}$	$-I_{CBO}$	-	-	100	nA	
Emitter Base Cutoff Current at $-V_{EB} = 6\text{ V}$	$-I_{EBO}$	-	-	100	nA	
Collector Base Breakdown Voltage at $-I_C = 50\ \mu\text{A}$	$-V_{(BR)CBO}$	60	-	-	V	
Collector Emitter Breakdown Voltage at $-I_C = 1\text{ mA}$	$-V_{(BR)CEO}$	50	-	-	V	
Emitter Base Breakdown Voltage at $-I_E = 50\ \mu\text{A}$	$-V_{(BR)EBO}$	6	-	-	V	
Collector Emitter Saturation Voltage at $-I_C = 50\text{ mA}$, $-I_B = 5\text{ mA}$	$-V_{CE(sat)}$	-	-	0.5	V	
Transition Frequency at $-V_{CE} = 12\text{ V}$, $I_E = 2\text{ mA}$, $f = 30\text{ MHz}$	f_T	-	140	-	MHz	
Output Capacitance at $-V_{CB} = 12\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	-	5	pF	

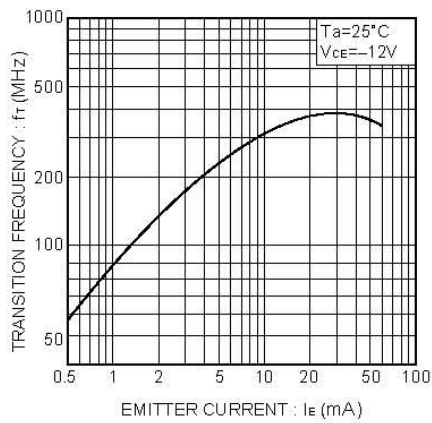
TOP DYNAMIC



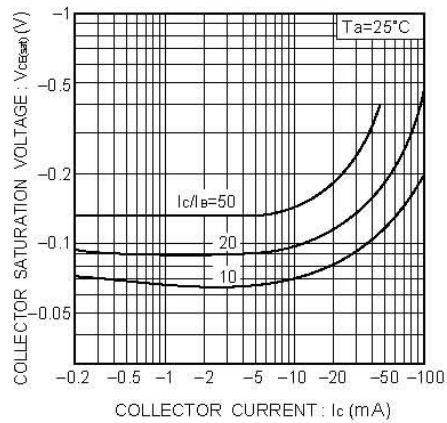
DC current gain vs. collector current



Grounded emitter output characteristics



Gain bandwidth product vs. emitter current



Collector-emitter saturation voltage vs. collector current